

Silicon PNP Power Transistors

2SB856

**DESCRIPTION**

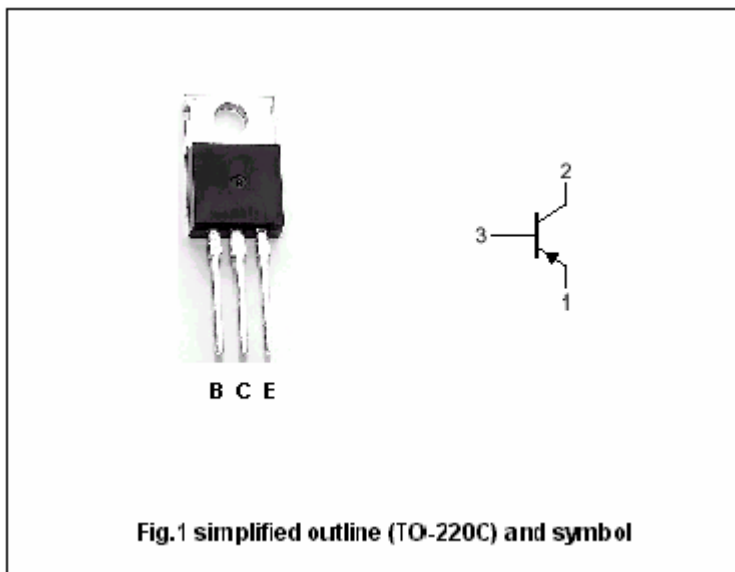
- With TO-220C package
- Low collector saturation voltage

**APPLICATIONS**

- Low frequency power amplifier

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings(Tc=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	-50	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-50	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-4	V
I <sub>C</sub>	Collector current		-3	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	25	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-45~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA; R <sub>BE</sub> =∞	-50			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-5mA; I <sub>E</sub> =0	-50			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-5mA; I <sub>C</sub> =0	-4			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-2 A; I <sub>B</sub> =-0.2 A			-1.2	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-4V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-20V; I <sub>E</sub> =0			-100	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-4V	35		200	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-0.1A ; V <sub>CE</sub> =-4V	35			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-4V		35		MHz

◆ h<sub>FE-1</sub> classifications

A	B	C
35-70	60-120	100-200

PACKAGE OUTLINE

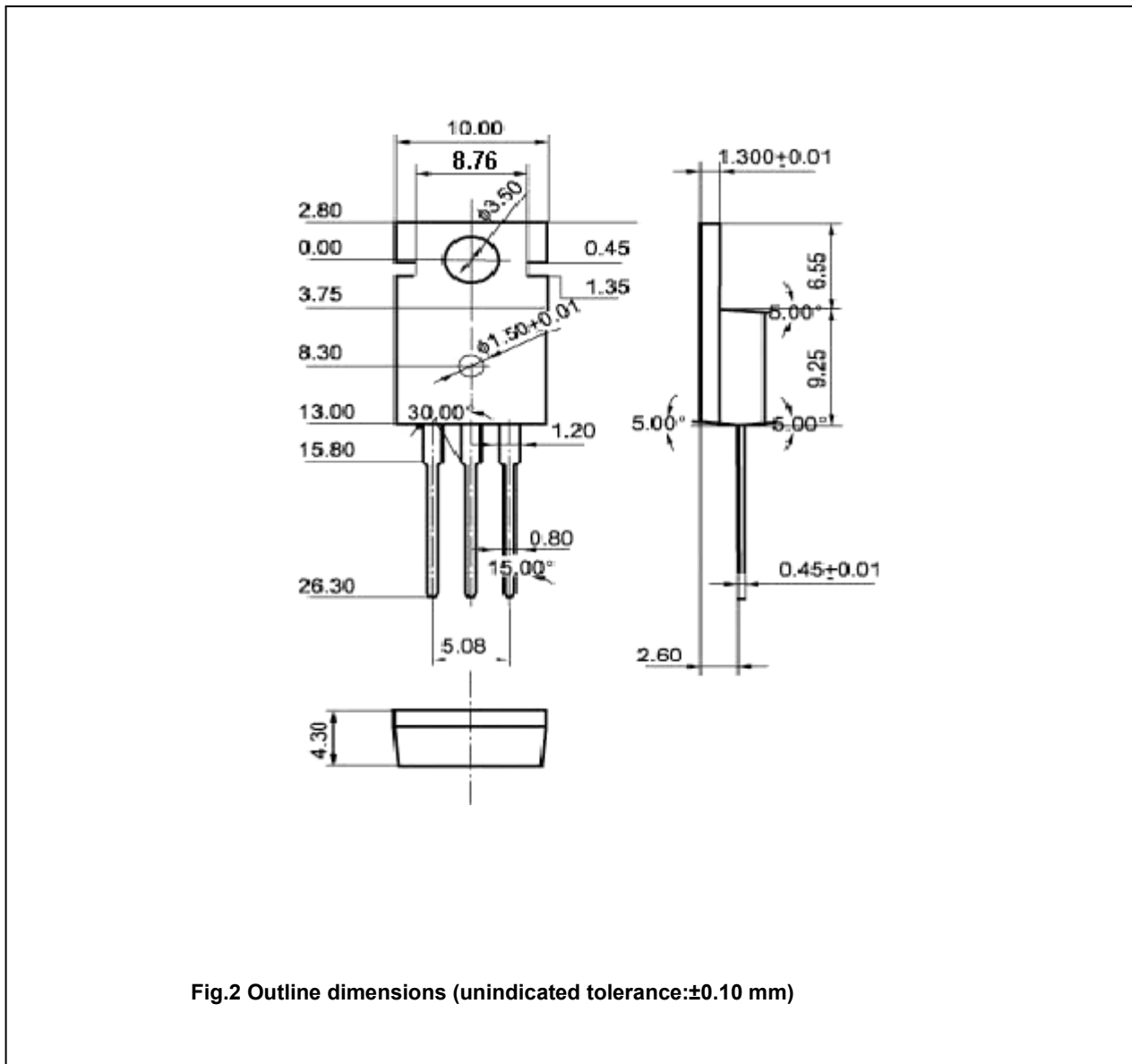


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)